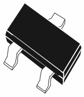
Central™
Semiconductor Corp.

NEW

CMSD2004S

HIGH VOLTAGE SWITCHING DIODE

SUPER™ mini



SOT-323 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CMSD2004S type is a silicon switching diode manufactured by the epitaxial planar process, designed for applications requiring high voltage capability.

The following configurations are available:

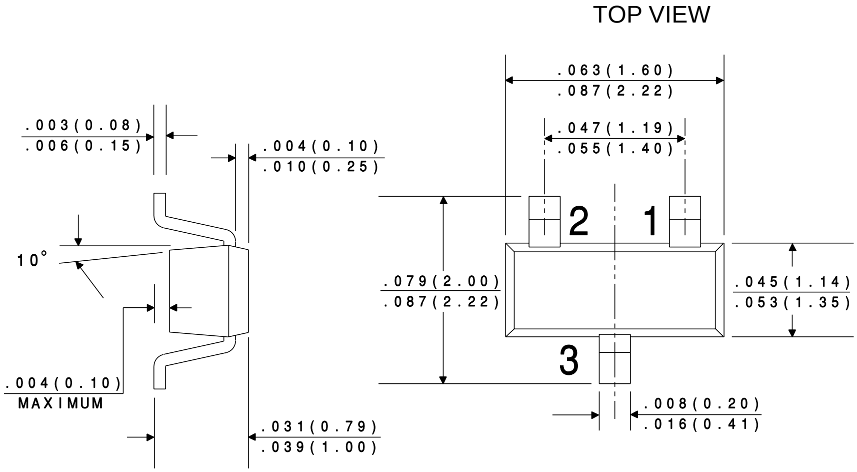
CMSD2004S DUAL, IN SERIES MARKING CODE: B6D

MAXIMUM RATINGS (T_A=25°C)	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	240	V
Peak Repetitive Reverse Voltage	V_{RRM}	300	V
Peak Repetitive Reverse Current	I_O	200	mA
Continuous Forward Current	I_F	225	mA
Peak Repetitive Forward Current	I_{FRM}	625	mA
Forward Surge Current, tp=1 µs	I_{FSM}	4000	mA
Forward Surge Current, tp=1 s	I_{FSM}	1000	mA
Power Dissipation	P_D	250	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	500	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
BV_R	I_R=100µA	300		V
I_R	V_R=200V		-	nA
I_R	V_R=200V, T_A=150°C		-	µA
I_R	V_R=240V		100	nA
I_R	V_R=240V, T_A=150°C		100	µA
V_F	I_F=100mA		1.0	V
C_T	V_R=0, f=1 MHz		5.0	pF
t_{rr}	I_F=I_R=30mA, RECOV. TO 3.0mA,R_L=100Ω		50	ns

All dimensions in inches (mm).



LEAD CODE